



Rev.A.1.1

3282.0(4)716(1)25.1(1)325.81344.52T(04)1(04)(ref 325.81344.52T(04)1(04)(

of large current, JCT151C-650RH of silicon controlled rectifiers provides high dV C H

$I_j=150\text{ }\mu\text{A}$	$P_{G(AV)}$	1	W
	P_{GM}	10	W
$I_j=25\text{ }\mu\text{A}$; non-repetitive,off-state;FIG.7)	V_{pp}	0.7	kV

JieJie Microelectronics Co., Ltd.

ELECTRICAL CHARACTERISTICS (T_j=25℃ unless otherwise specified)

Symbol	Test Condition	Value			Unit
		MIN.	TYP.	MAX.	
I_{GT}	$V_D=12V\ R_L=33\Omega$	-	-	15	mA

$V_{GT} \leq 0.012V$ $C_{iss} \leq 5.2pF$ $t_{on} \leq 10\mu s$ $M_1 < M_{CI.16}$ $(f_{osc} \leq 120kHz)$ $r_{DS(on)} \leq 522.68m\Omega$ $(V_{GS}=10V)$ $V_{DS} \leq 5.36V$ $(f_{osc} \leq 100kHz)$ $T_w \leq 788\mu s$ $r_{DS(on)} \leq 0.48\Omega$

ORDERING INFORMATION

<u>J</u>	<u>CT</u>	<u>151</u>	<u>C</u>	<u>-650R</u>	<u>H</u>
JieJie Microelectronics Co., Ltd.	SCRs	$I_{T(RMS)}:12A$	C:TO-220C	650R: V_{DRM}/V_{RRM} 650V	High junction temperature

MARKING

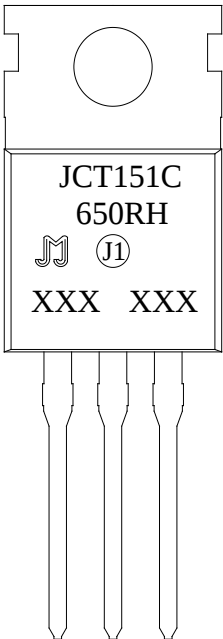
	<u>XXX</u> <u>XXX</u> Year _____ Month _____ Production Code
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FIG.1: Maximum power dissipation versus RMS on-state current

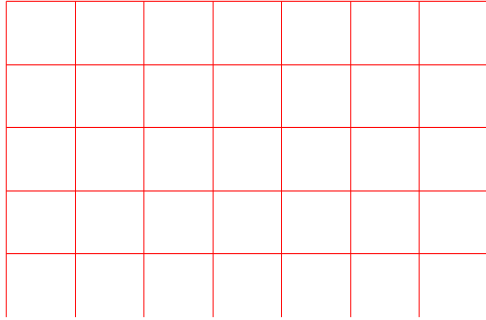
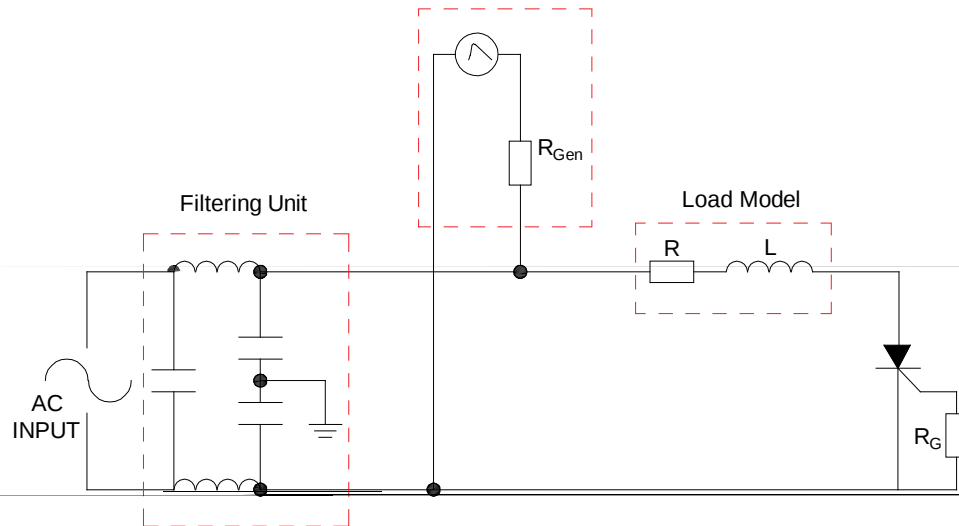


FIG.2: RMS on-state current versus case temperature

FIG.7 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards.

IEC61000-4-5 Standards
Surge Generator

JCT151C-650RH

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